
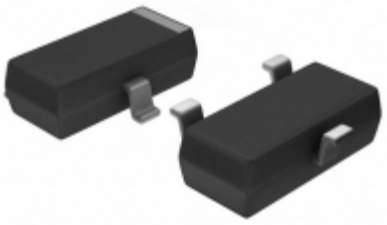
	<p>SI2327DS-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI2327DS-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET P-CH 200V 0.38A SOT-23</p> <p>Datenblätter:  SI2327DS-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 30238 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI2327DS-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET P-CH 200V 0.38A SOT-23
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	30238 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	750mW (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	200V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	380mA (Ta)
Rds On (Max) @ Id, Vgs	2.35 Ohm @ 500mA, 10V
VGS (th) (Max) @ Id	4.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	12nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	510pF @ 25V
Verpackung	Tape & Reel (TR)


























SI2327DS-T1-GE3 ist neu im Original, Suche SI2327DS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2327DS-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI2327DS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2327DS-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 200V 0.38A SOT23-3</p>	 <p>SI2326DS-T1-GE3 VISHAY VISHAY SOT23</p>	 <p>SI2327DS-T1-E3 Vishay / Siliconix MOSFET P-CH 200V 0.38A SOT23-3</p>	 <p>SI2326DS-T1-E3 VISHAY VISHAY SOT23</p>
 <p>SI2327DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 200V 0.38A SOT-23</p>	 <p>SI2328DS-T1 VISHAY SI2328DS-T1 VISHAY</p>	 <p>SI2328DS VISHAY SI2328DS VISHAY</p>	 <p>SI2328DS-T1-E3 Vishay / Siliconix MOSFET N-CH 100V 1.15A SOT23-3</p>

heiße Teile

Mehr

 SI2321DS-T1-E3	 SI2321DS-T1-GE3	 SI2321DS-T1-GE3	 SI2323CDS-T1	 SI2323CDS-T1-E3
 SI2323CDS-T1-GE3	 SI2323CDS-T1-GE3	 SI2323DDS-T1-E3	 SI2323DDS-T1-GE3	 SI2323DDS-T1-GE3
 SI2323DS	 SI2323DS-T1-E3	 SI2323DS-T1-E3	 SI2323DS-T1-GE3	 SI2323DS-T1-GE3
 SI2324DS-T1-E3	 SI2324DS-T1-GE3	 SI2324DS-T1-GE3	 SI2325DS-T1-E3	 SI2325DS-T1-E3
 SI2325DS-T1-GE3	 SI2325DS-T1-GE3	 SI2327DS-T1-E3	 SI2327DS-T1-E3	 SI2327DS-T1-GE3
 SI2328DS	 SI2328DS-T1	 SI2328DS-T1-E3	 SI2328DS-T1-E3	 SI2328DS-T1-GE3
 SI2328DS-T1-GE3	 SI2329DS-T1-E3	 SI2329DS-T1-GE3	 SI2329DS-T1-GE3	 SI2331DS
 SI2331DS-T1-E3	 SI2331DS-T1-E3	 SI2331DS-T1-GE3	 SI2331DS-T1-GE3	 SI2333ADS-T1-GE3
 SI2333CDS	 SI2333CDS-T1-E3	 SI2333CDS-T1-E3	 SI2333CDS-T1-GE3	 SI2333CDS-T1-GE3
 SI2333DDS-T1-E3	 SI2333DDS-T1-GE3	 SI2333DDS-T1-GE3	 SI2333DS	 SI2333DS-T1-E3

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